3DA102

NPN Silicon High Frequency High Power Transistor

Features:

1. Excellent second breakdown capacity. Good characteristic frequency.
2. Amplification factor of small current is great. Good voltage resistance.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for analog computer power output, amplification of high frequency,middle frequency and low frequency, switching circuit.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications	Test Condition
Total Dissipation	P_{tot}	W	7.5	Tc:75°C
Max. Collector Current	I_{CM}	A	1.0	
Junction Temperature	T_{jm}	°C	175	
Storage Temperature	T_{stg}	°C	-55~+175	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	30~50	I_C=2mA
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	5	I_E=2mA
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	1.5	I_C=0.5A, I_B=0.1A
Collector-Emitter Leakage Current	I_{CEO}	mA	2.0	V_{CE}=20V
Emitter-Base Leakage Current	I_{EBO}	mA	2.0	V_{EB}=5V
DC Current Gain	h_{FE}		10	V_{CE}=5V, I_C=0.3A
Transition frequency	f_T	MHz	100	V_{CE}=5V, I_C=0.2A f_O=10 MHz

Outline and Dimensions: